



DZ4J043K0R

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 9J

■ Basic Part Number :
Dual DZ2J043 (Parallel)

■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±15	kV
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) *1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm)
Solder in (0.8 mm x 0.8 mm)
*2: Test method:IEC61000_4_2(C = 150 pF,R = 330 Ω, Contact discharge:10 times)

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 10 mA			1.0	V
Zener voltage ^{*1, *2}	V _Z	I _Z = 5 mA	4.09		4.52	V
Zener operating resistance	R _Z	I _Z = 5 mA			130	Ω
Reverse current	I _R	V _R = 1 V			10	μA
Temperature coefficient of zener voltage ^{*3}	SZ	I _Z = 5 mA		-0.9		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.
2. Absolute frequency of input and output is 5 MHz.
3. *1: The temperature must be controlled 25 °C for V_Z measurement.
V_Z value measured at other temperature must be adjusted to V_Z (25 °C)
*2: V_Z guaranteed 20 ms after current flow.
*3: T_j = 25 °C to 150 °C

